

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 05-175145  
(43)Date of publication of application : 13.07.1993

(51)Int.CI. H01L 21/205  
C23C 16/24  
C23C 16/52  
C30B 23/02  
C30B 25/14

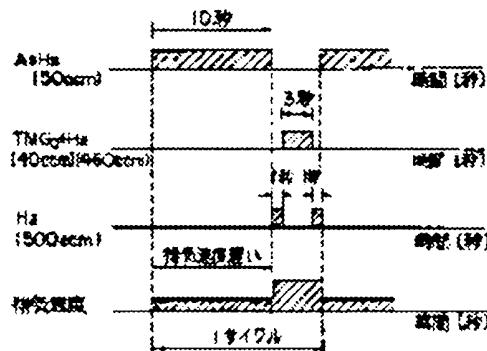
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## (54) CRYSTAL GROWTH METHOD

### (57)Abstract:

**PURPOSE:** To provide a crystal growth method improved in the efficiency of use of a feedstock gas at the time of growing III-V compound semiconductor crystal with the use of atomic layer epitaxy method in the crystal growth method using the atomic layer epitaxy method for alternately supplying feedstock gases out of crystal growth techniques of compound semiconductor.

**CONSTITUTION:** In a crystal growth method using atomic layer epitaxy method for growing III-V compound semiconductor crystal on a semiconductor substrate surface by alternately supplying group III feedstock gas and group V feedstock gas, the linear velocity of the group V feedstock gas flowing on the semiconductor substrate surface at the time of growing the crystal is made slower than the linear velocity of group III feedstock gas.



## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision]